

ABSTRACT OF THE DISCLOSURE

A solid-state imaging device, comprises an image pickup unit having unit cells including opto-electrical converter elements, said unit cells being disposed in two-dimensional array, a selection line made of polysilicon for selectively determining the unit cells in the same row within the image pickup unit, a read-out line made of polysilicon for reading out electric charge accumulated in the opto-electrical converter elements of the unit cells in the same row within the image pickup unit, a signal line transmitting pixel signals produced from the unit cells in the same row within the image pickup unit, a reset line made of polysilicon for discharging the unit cells in the same row within the image pickup unit down to the desired voltage level, a driver circuit located on one side of the image pickup unit for supplying drive signals to the read-out line, the selection line, and the reset line, respectively, and a read-out auxiliary wiring disposed along at least the read-out line and electrically connected to the read-out line at a plurality of junctions, the read-out auxiliary wiring being of relatively lower electric resistivity than the read-out line.